

AMENDMENTS TO THE CLAIMS

Claim 1. (currently amended) A method for manufacturing a multi-slants reflector[[,]] comprising the steps of:

5 providing a substrate;

forming a plurality of thin film transistors and a plurality of multi-layered structures on the substrate simultaneously;[[and]]

coating an organic layer on said thin film transistors and

10 said multi-layered structures;

performing a baking step to smooth the organic layer so as to form a plurality of asymmetric slants; and

forming a reflective metal layer on the organic layer[[.]];

15 wherein each of said asymmetric slants comprises said multi-layered structure, and each layer of said multi-layered structure has substantially different widths.

20 Claim 2. (original) The method of claim 1 for manufacturing a multi-slants reflector, wherein each of said asymmetric slants has substantially different angles between an upper surface of the reflective metal layer and an upper surface of the substrate.

Claim 3. (original) The method of claim 1 for manufacturing
a multi-slants reflector, wherein each of said asymmetric
slants has substantially different heights.

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Claim 4. (canceled)

Claim 5. (currently amended) The method of ~~claim 4~~ claim 1
for manufacturing a multi-slants reflector, wherein said
10 multi-layered structure is a random composition of a gate
metal layer, an insulation layer, an a-Si layer, an N⁺ layer,
and a source/drain metal layer.

Claim 6. (original) The method of claim 2 for manufacturing
15 a multi-slants reflector, wherein said angles range from
0 degrees to approximately 10 degrees.

Claim 7. (currently amended) A multi-slants reflector applied
in a liquid crystal display (LCD), the multi-slants
20 reflector comprising:
a substrate;
a plurality of thin film transistors disposed on the
substrate;
a reflective metal layer;

a plurality of asymmetric slants, each comprising a
multi-layered structure, located between the
substrate and the reflective metal layer; and
an organic layer located between said reflective metal
5 layer and said multi-layered structure;
wherein each layer of said multi-layered structure has
substantially different widths.

Claim 8. (original) A multi-slants reflector according to
10 claim 7, wherein each of said asymmetric slants has
substantially different angles between an upper surface
of the reflective metal layer and an upper surface of the
substrate.

15 Claim 9. (original) A multi-slants reflector according to
claim 7, wherein each of said asymmetric slants has
substantially different heights.

Claim 10 (canceled)

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Claim 11. (original) A multi-slants reflector according to
claim 7, wherein said multi-layered structure is a random
composition of a gate metal layer, an insulation layer,
an a-Si layer, an N⁺ layer, and a source/drain metal layer.

Claim 12. (original) A multi-slants reflector according to
claim 8, wherein said angles range from 0 degrees to
approximately 10 degrees.

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Claim 13. (currently amended) A method for manufacturing a
multi-slants reflector[[,]] comprising the steps of:
providing a substrate;

forming a plurality of thin film transistors and a
10 plurality of multi-layered structures on the
substrate simultaneously;

coating a protection layer on said thin film transistors
and said multi-layered structures; and
forming a reflective metal layer on said protection layer;
15 wherein each layer of said multi-layered structure has
substantially different widths.

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